

Method for growing $\text{CuBiP}_2\text{Se}_6$ using method for directed melt crystallization involves stepwise heating of evacuated quartz ampoules containing the elemental components - bismuth, phosphorus, and selenium - in a stoichiometric ratio. $\text{CuBiP}_2\text{Se}_6$ is grown in evacuated quartz ampoules using directional solidification from the melt at a temperature of 860 K and holding at this temperature for 24 hours, as well as a 630 K annealing zone followed by annealing for 48 hours to homogenize melt of resulting batch at a growth rate of 0.4-0.5 mm/h, after which single crystal is cooled to room temperature at a rate of 4-5 K/h.